HEXFET®
Power MOSFET, 180 A

SOT-227

FEATURES

- Fully isolated package
- Easy to use and parallel
- Very low on-resistance
- Dynamic dV/dt rating
- Fully avalanche rated
- Simple drive requirements
- Low drain to case capacitance
- Low internal inductance
- UL pending
- Totally lead (Pb)-free

Pb-free
RoHS COMPLIANT

PRODUCT SUMMARY	
V_{DSS}	100 V
I_D DC	180 A
$R_{DS(on)}$	0.0065 Ω

DESCRIPTION

5th Generation, high current density HEXFETs® are paralled into a compact, high power module providing the best combination of switching, ruggedized design, very low on resistance and cost effectiveness.
The isolated SOT-227 package is preferred for all commercial-industrial applications at power dissipation levels to approximately 500 W. The low thermal resistance and easy connection to the SOT-227 package contribute to its universal acceptance throughout the industry.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Continuous drain current at V_{GS} 10 V	I_D	T_C = 25 °C	180	A
		T_C = 100 °C	120	
Pulsed drain current	I_{DM} (1)		720	
Power dissipation	P_D	T_C = 25 °C	480	W
Linear derating factor			2.7	W/°C
Gate to source voltage	V_{GS}		± 20	V
Single pulse avalanche energy	E_{AS} (2)		700	mJ
Avalanche current	I_{AR} (1)		180	A
Repetitive avalanche energy	E_{AR} (1)		48	mJ
Peak diode recovery dV/dt	dV/dt (3)		5.7	V/ns
Operating junction and storage temperature range	T_J, T_{Stg}		- 55 to + 150	°C
Insulation withstand voltage (AC-RMS)	V_{ISO}		2.5	kV
Mounting torque		M4 screw	1.3	Nm

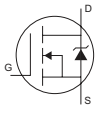
Notes
(1) Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
(2) Starting T_J = 25 °C, L = 43 µH, R_g = 25 Ω, I_{AS} = 180 A (see fig. 12)
(3) I_{SD} ≤ 180 A, dI/dt ≤ 83 A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150 °C

THERMAL RESISTANCE				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNITS**
Junction to case	$R_{\theta JC}$	-	0.26	°C/W
Case to sink, flat, greased surface	$R_{\theta CS}$	0.05	-	

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Drain to source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	100	-	-	V
Breakdown voltage temperature coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	Reference to 25 °C, I_D = 1 mA	-	0.093	-	V/°C
Static drain to source on-resistance	$R_{DS(on)}$ (1)	V_{GS} = 10 V, I_D = 180 A	-	0.0065	-	Ω
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0	-	4.0	V
Forward transconductance	g_{fs}	V_{DS} = 25 V, I_D = 180 A	93	-	-	S
Drain to source leakage current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V	-	-	50	µA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 125 °C	-	-	500	
Gate to source forward leakage	I_{GSS}	V_{GS} = 20 V	-	-	200	nA
		V_{GS} = - 20 V	-	-	- 200	
Total gate charge	Q_g	I_D = 180 A V_{DS} = 80 V V_{GS} = 10.0 V; see fig. 6 and 13 (1)	-	250	380	nC
Gate to source charge	Q_{gs}		-	40	60	
Gate to drain ("Miller") charge	Q_{gd}		-	110	165	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 50 V I_D = 180 A R_G = 2.0 Ω (internal) R_D = 0.27 Ω, see fig. 10 (1)	-	45	-	ns
Rise time	t_r		-	351	-	
Turn-off delay time	$t_{d(off)}$		-	181	-	
Fall time	t_f		-	335	-	
Internal source inductance	L_S	Between lead, and center of die contact	-	5.0	-	nH
Input capacitance	C_{iss}	V_{GS} = 0 V V_{DS} = 25 V f = 1.0 MHz, see fig. 5	-	10 700	-	pF
Output capacitance	C_{oss}		-	2800	-	
Reverse transfer capacitance	C_{rss}		-	1300	-	

Note

(1) Pulse width ≤ 300 µs, duty cycle ≤ 2 %

SOURCE-DRAIN RATINGS AND CHARACTERISTICS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Continuous source current (body diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 	-	-	180	A
Pulsed source current (body diode)	I_{SM} (1)		-	-	720	
Diode forward voltage	V_{SD} (2)	T_J = 25 °C, I_S = 180 A, V_{GS} = 0 V	-	-	1.3	V
Reverse recovery time	t_{rr} (2)	T_J = 25 °C, I_F = 180 A; dI/dt = 100 A/µs	-	300	450	ns
Reverse recovery charge	Q_{rr}		-	2.6	3.9	µC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S + L_D)				

Notes

(1) Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

(2) Pulse width ≤ 300 µs, duty cycle ≤ 2 %

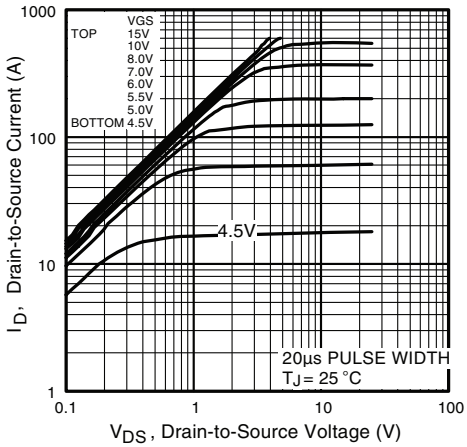


Fig. 1 - Typical Output Characteristics

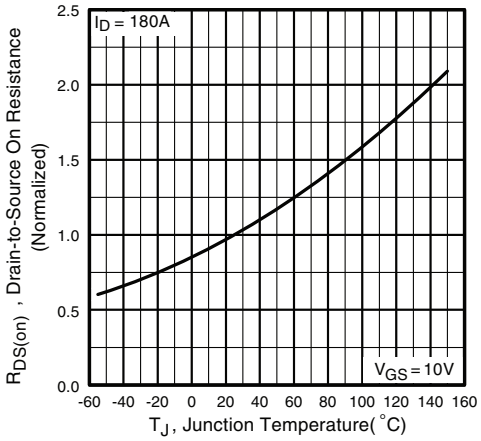


Fig. 4 - Normalized On-Resistance vs. Temperature

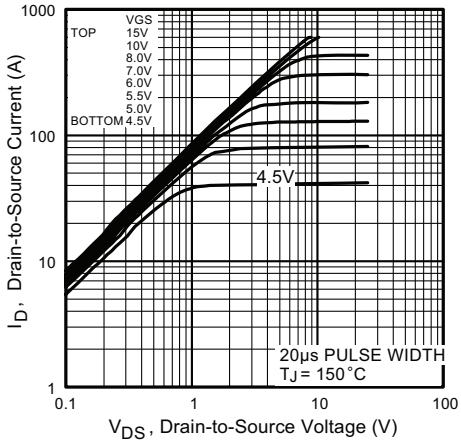


Fig. 2 - Typical Output Characteristics

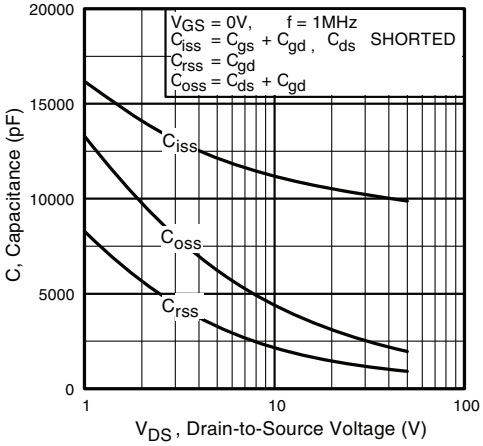


Fig. 5 - Typical Capacitance vs. Drain to Source Voltage

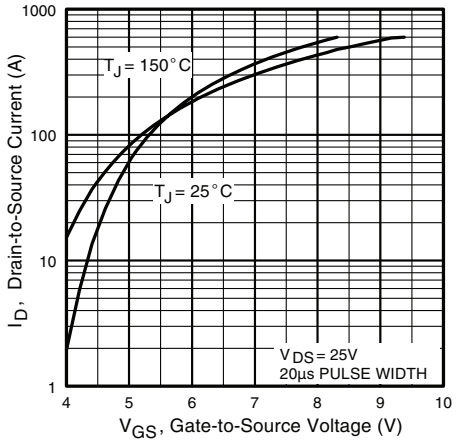


Fig. 3 - Typical Transfer Characteristics

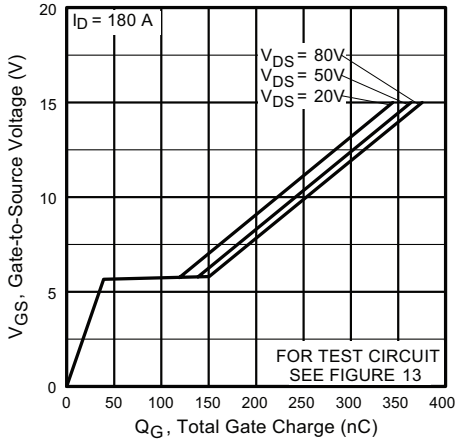


Fig. 6 - Typical Gate Charge vs. Gate to Source Voltage

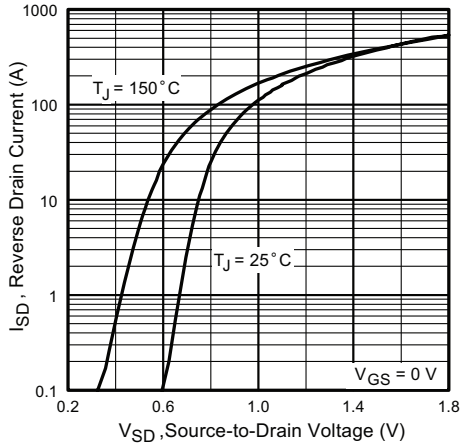


Fig. 7 - Typical Source Drain Diode Forward Voltage

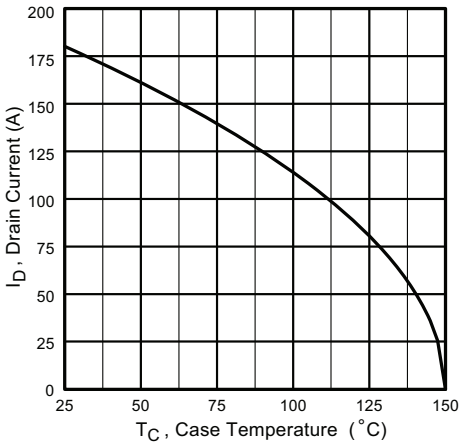


Fig. 9 - Maximum Drain Current vs. Case Temperature

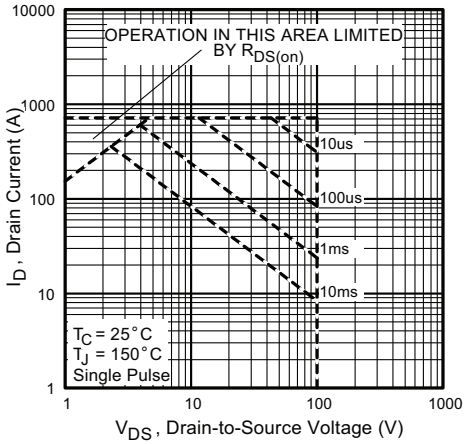


Fig. 8 - Maximum Safe Operating Area

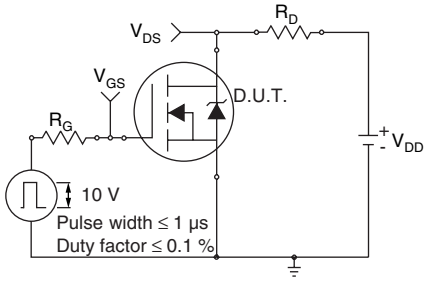


Fig. 10a - Switching Time Test Circuit

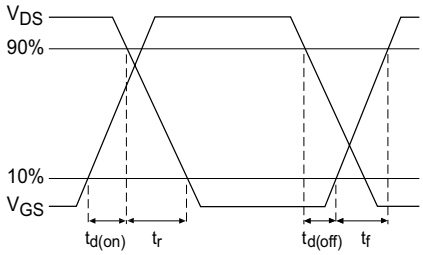


Fig. 10b - Switching Time Waveforms

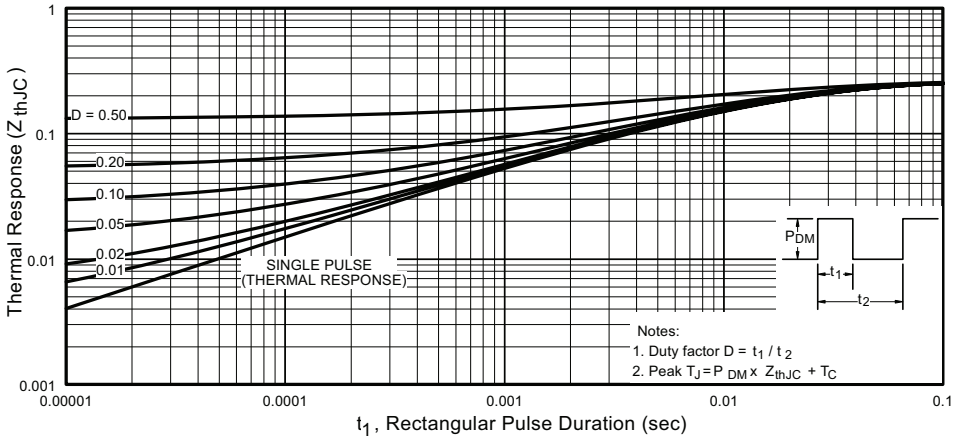


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction to Case

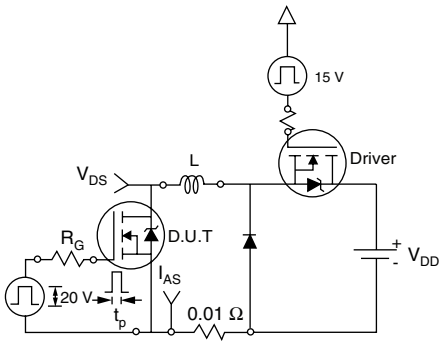


Fig. 12a - Unclamped Inductive Test Circuit

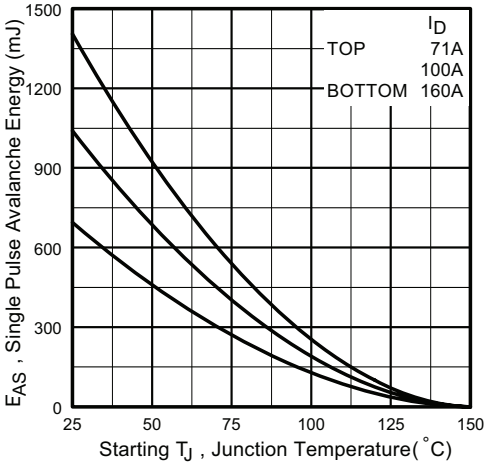


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

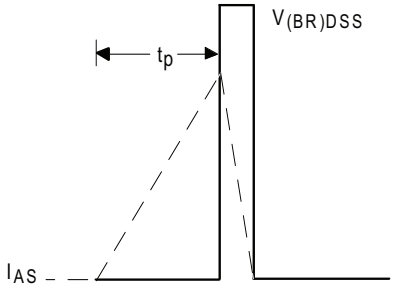


Fig. 12b - Unclamped Inductive Waveforms

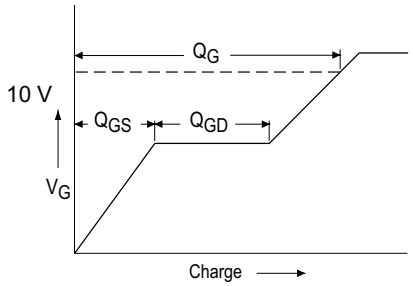


Fig. 13a - Basic Gate Charge Waveform

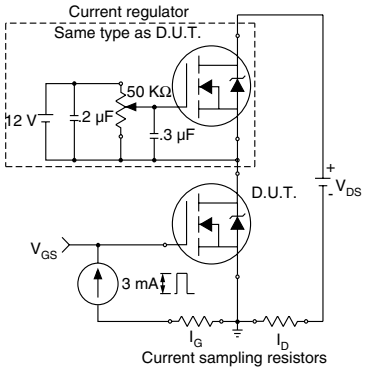


Fig. 13b - Gate Charge Test Circuit

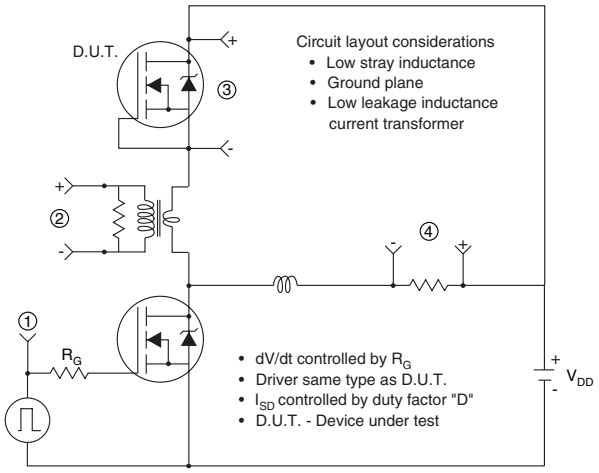
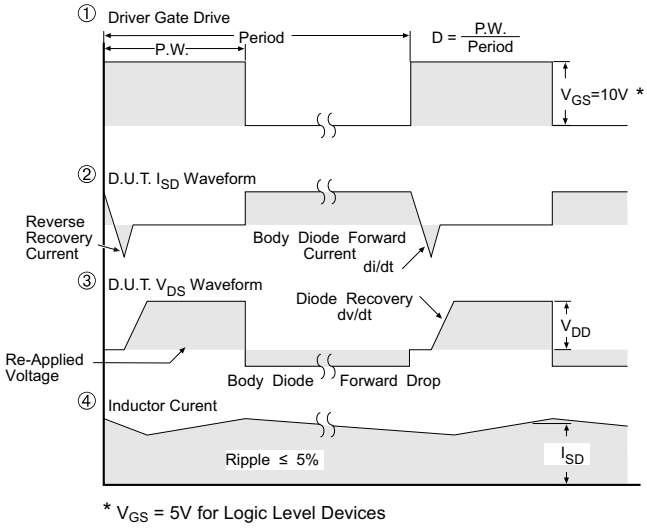


Fig. 13c - Peak Diode Recovery dV/dt Test Circuit



* V_{GS} = 5V for Logic Level Devices

Fig. 14 - For N-Channel HEXFET® Power MOSFETs

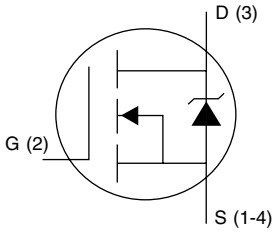
ORDERING INFORMATION TABLE

Device code

F	B	180	S	A	10	P
1	2	3	4	5	6	7

1 - HEXFET® Power MOSFET
2 - Generation 5 HEXFET MOSFET silicon DBC construction
3 - Current rating (180 = 180 A)
4 - Single switch
5 - SOT-227
6 - Voltage rating (10 = 100 V)
7 - P = Lead (Pb)-free

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95036
Packaging information	http://www.vishay.com/doc?95037

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